# 2SD2242, 2SD2242A

### Silicon NPN triple diffusion planar type Darlington

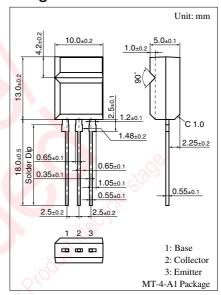
#### For power amplification

#### ■ Features

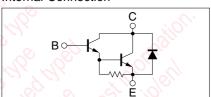
- High forward current transfer ratio h<sub>FE</sub>
- High-speed switching
- Allowing supply with the radial taping

#### ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter		Symbol	Rating	Unit
Collector to base	2SD2242	V <sub>CBO</sub>	60	V
voltage	2SD2242A		80	
Collector to	2SD2242	V <sub>CEO</sub>	60	V
emitter voltage	2SD2242A		80	
Emitter to base voltage		V <sub>EBO</sub>	5	V
Peak collector current		I <sub>CP</sub>	8	A
Collector current		$I_{C}$	4	A
Collector power	$T_C = 25^{\circ}C$	$P_{\rm C}$	15	W
dissipation	$T_a = 25^{\circ}C$		2	j
Junction temperature		T <sub>j</sub>	150	°C/0
Storage temperature		T <sub>stg</sub>	-55 to +150	°C



#### Internal Connection



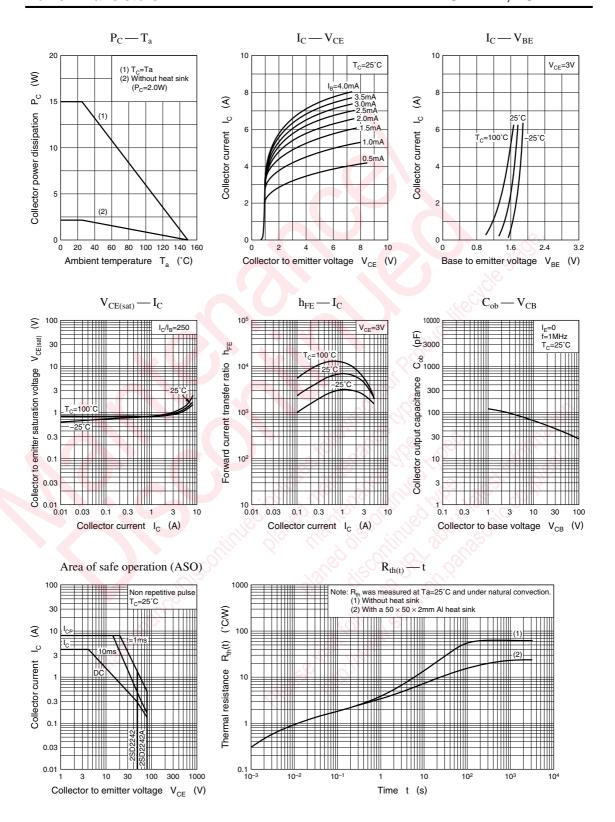
#### ■ Electrical Characteristics $T_C = 25$ °C

Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Collector cutoff	2SD2242	I <sub>CBO</sub>	$V_{CB} = 60 \text{ V}, I_{E} = 0$	-07/		200	μΑ
current	2SD2242A	FILD)	$V_{CB} = 80 \text{ V}, I_{E} = 0$	10	(5)	200	
Collector cutoff	2SD2242	$I_{CEO}$	$V_{CE} = 30 \text{ V}, I_{B} = 0$	2		500	μΑ
current	2SD2242A	50	$V_{CE} = 40 \text{ V}, I_{B} = 0$	1.7		500	
Emitter cutoff current	col	$I_{EBO}$	$V_{EB} = 5 \text{ V}, I_{C} = 0$			2	μΑ
Collector to emitter	2SD2242	V <sub>CEO</sub>	$I_C = 30 \text{ mA}, I_B = 0$	60			V
voltage	2SD2242A			80			
Forward current transfe	er ratio	h <sub>FE1</sub>	$V_{CE} = 3 \text{ V}, I_{C} = 0.5 \text{ A}$	1 000			
		h <sub>FE2</sub> *	$V_{CE} = 3 \text{ V}, I_{C} = 3 \text{ A}$	2 000		10 000	
Base to emitter voltage	:	V <sub>BE</sub>	$V_{CE} = 3 \text{ V}, I_{C} = 3 \text{ A}$			2.5	V
Collector to emitter satu	ration voltage	V <sub>CE(sat)</sub>	$I_C = 3 \text{ A}, I_B = 12 \text{ mA}$			2	V
			$I_C = 5 \text{ A}, I_B = 20 \text{ mA}$			4	
Transition frequency		$f_T$	$V_{CE} = 10 \text{ V}, I_C = 0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Turn-on time		t <sub>on</sub>	$I_C = 3 \text{ A}, I_{B1} = 12 \text{ mA}, I_{B2} = -12 \text{ mA},$		0.5		μs
Storage time		t <sub>stg</sub>	$V_{CC} = 50 \text{ V}$		4		μs
Fall time		$t_{\rm f}$			1		μs

Note) \*: Rank classification

Rank	Q	R
h <sub>FE2</sub>	2 000 to 5 000	4 000 to 10 000

350 Panasonic



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